

# Kaoru Toko

## List of Publications by Year in descending order

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271  
papers

5,171  
citations

101384

36  
h-index

155451

55  
g-index

273  
all docs

273  
docs citations

273  
times ranked

1438  
citing authors

#	ARTICLE	IF	CITATIONS
1	Electrical properties of poly-Ge on glass substrate grown by two-step solid-phase crystallization. Solid-State Electronics, 2009, 53, 1159-1164.	0.8	137
2	Investigation of grain boundaries in BaSi <sub>2</sub> epitaxial films on Si(1 1 1) substrates using transmission electron microscopy and electron-beam-induced current technique. Journal of Crystal Growth, 2012, 348, 75-79.	0.7	133
3	Flux creep and irreversibility line in high-temperature oxide superconductors. Applied Physics Letters, 1990, 56, 2039-2041.	1.5	120
4	Effect of amorphous Si capping layer on the hole transport properties of BaSi <sub>2</sub> and improved conversion efficiency approaching 10% in p-BaSi <sub>2</sub> /n-Si solar cells. Applied Physics Letters, 2016, 109, .	1.5	109
5	Low-temperature (180°C) formation of large-grained Ge (111) thin film on insulator using accelerated metal-induced crystallization. Applied Physics Letters, 2014, 104, .	1.5	96
6	High-Electrical-Conductivity Multilayer Graphene Formed by Layer Exchange with Controlled Thickness and Interlayer. Scientific Reports, 2019, 9, 4068.	1.6	89
7	Highly (111)-oriented Ge thin films on insulators formed by Al-induced crystallization. Applied Physics Letters, 2012, 101, 072106.	1.5	88
8	Giant Ge-on-Insulator Formation by Si-Ge Mixing-Triggered Liquid-Phase Epitaxy. Applied Physics Express, 0, 2, 045503.	1.1	87
9	Investigation of the recombination mechanism of excess carriers in undoped BaSi <sub>2</sub> films on silicon. Journal of Applied Physics, 2012, 112, .	1.1	84
10	Multichannel taste sensor using electric potential changes in lipid membranes. Biosensors and Bioelectronics, 1994, 9, 359-364.	5.3	81
11	Influence of grain size and surface condition on minority-carrier lifetime in undoped n-BaSi <sub>2</sub> on Si(111). Journal of Applied Physics, 2014, 115, .	1.1	80
12	Perpendicular magnetic anisotropy of Mn <sub>4</sub> N films on MgO(001) and SrTiO <sub>3</sub> (001) substrates. Journal of Applied Physics, 2014, 115, .	1.1	77
13	High-quality single-crystal Ge stripes on quartz substrate by rapid-melting-growth. Applied Physics Letters, 2009, 95, .	1.5	75
14	Determination of Bulk Minority-Carrier Lifetime in BaSi <sub>2</sub> Earth-Abundant Absorber Films by Utilizing a Drastic Enhancement of Carrier Lifetime by Post-Growth Annealing. Applied Physics Express, 2013, 6, 112302.	1.1	75
15	Temperature dependent metal-induced lateral crystallization of amorphous SiGe on insulating substrate. Applied Physics Letters, 2006, 89, 182120.	1.5	73
16	In-situ heavily p-type doping of over 10 <sup>20</sup> cm <sup>-3</sup> in semiconducting BaSi <sub>2</sub> thin films for solar cells applications. Applied Physics Letters, 2013, 102, .	1.5	72
17	High-hole mobility polycrystalline Ge on an insulator formed by controlling precursor atomic density for solid-phase crystallization. Scientific Reports, 2017, 7, 16981.	1.6	71
18	p-BaSi <sub>2</sub> /n-Si heterojunction solar cells with conversion efficiency reaching 9.0%. Applied Physics Letters, 2016, 108, .	1.5	69

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19	700°C synthesis of high-Sn content (25%) GeSn on insulator by Sn-induced crystallization of amorphous Ge. Applied Physics Letters, 2015, 106, .	1.5	64
20	Molecular beam epitaxy of BaSi <sub>2</sub> thin films on Si(001) substrates. Journal of Crystal Growth, 2012, 345, 16-21.	0.7	61
21	Ni-imprint induced solid-phase crystallization in Si <sub>1-x</sub> Ge <sub>x</sub> (x: 0~1) on insulator. Applied Physics Letters, 2007, 91, .	1.5	60
22	Current-voltage characteristics and self-sustained oscillations in dioleoyl phosphate-millipore membranes. Biophysical Chemistry, 1984, 20, 39-59.	1.5	58
23	Impact of Ba to Si deposition rate ratios during molecular beam epitaxy on carrier concentration and spectral response of BaSi <sub>2</sub> epitaxial films. Journal of Applied Physics, 2018, 123, 045703.	1.1	55
24	Improving carrier mobility of polycrystalline Ge by Sn doping. Scientific Reports, 2018, 8, 14832.	1.6	51
25	Improved photoresponsivity of semiconducting BaSi <sub>2</sub> epitaxial films grown on a tunnel junction for thin-film solar cells. Applied Physics Letters, 2012, 100, 152114.	1.5	50
26	Metal-induced layer exchange of group IV materials. Journal Physics D: Applied Physics, 2020, 53, 373002.	1.3	50
27	Analysis of the electrical properties of Cr/n-BaSi <sub>2</sub> Schottky junction and n-BaSi <sub>2</sub> /p-Si heterojunction diodes for solar cell applications. Journal of Applied Physics, 2014, 115, .	1.1	49
28	Chip-size formation of high-mobility Ge strips on SiN films by cooling rate controlled rapid-melting growth. Applied Physics Letters, 2011, 99, 032103.	1.5	47
29	Operation of BaSi <sub>2</sub> homojunction solar cells on p <sup>+</sup> -Si(111) substrates and the effect of structure parameters on their performance. Applied Physics Express, 2019, 12, 041005.	1.1	47
30	Electrical characterization and conduction mechanism of impurity-doped BaSi <sub>2</sub> films grown on Si(111) by molecular beam epitaxy. Thin Solid Films, 2012, 522, 95-99.	0.8	45
31	Fabrication and characterization of polycrystalline BaSi <sub>2</sub> by RF sputtering. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1759-1761.	0.8	45
32	Orientation Control of Large-Grained Si Films on Insulators by Thickness-Modulated Al-Induced Crystallization. Crystal Growth and Design, 2013, 13, 1767-1770.	1.4	44
33	p-BaSi <sub>2</sub> /n-Si heterojunction solar cells on Si(001) with conversion efficiency approaching 10%: comparison with Si(111). Applied Physics Express, 2018, 11, 062301.	1.1	42
34	On the oscillatory phenomenon in an oil/water interface. Biophysical Chemistry, 1985, 22, 151-158.	1.5	40
35	Selective formation of large-grained, (100)- or (111)-oriented Si on glass by Al-induced layer exchange. Journal of Applied Physics, 2014, 115, .	1.1	40
36	Influence of air exposure duration and a-Si capping layer thickness on the performance of p-BaSi <sub>2</sub> /n-Si heterojunction solar cells. AIP Advances, 2016, 6, .	0.6	40

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37	Sign of the spin-polarization in cobalt-iron nitride films determined by the anisotropic magnetoresistance effect. <i>Journal of Applied Physics</i> , 2014, 116, .	1.1	39
38	Relation of growth process to spatial patterns of electric potential and enzyme activity in bean roots. <i>Biophysical Chemistry</i> , 1987, 27, 39-58.	1.5	35
39	Epitaxial growth and magnetic characterization of ferromagnetic Co <sub>4</sub> N thin films on SrTiO <sub>3</sub> (001) substrates by molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2011, 336, 40-43.	0.7	35
40	Perpendicular magnetic anisotropy in Co <sub>x</sub> Mn <sub>4-x</sub> N ( $x = 0$ and $0.2$ ) epitaxial films and possibility of tetragonal Mn <sub>4</sub> N phase. <i>AIP Advances</i> , 2016, 6, .	0.6	34
41	Low-Temperature ( $\sim 250^\circ\text{C}$ ) Cu-Induced Lateral Crystallization of Amorphous Ge on Insulator. <i>Electrochemical and Solid-State Letters</i> , 2011, 14, H274.	2.2	33
42	Stabilization effect of protons and divalent cations on membrane structures of lipids. <i>Biophysical Chemistry</i> , 1981, 14, 11-23.	1.5	32
43	Oscillations of electrical potential along a root of a higher plant. <i>Biophysical Journal</i> , 1990, 57, 269-279.	0.2	32
44	Formation of polycrystalline BaSi <sub>2</sub> films by radio-frequency magnetron sputtering for thin-film solar cell applications. <i>Thin Solid Films</i> , 2013, 534, 116-119.	0.8	32
45	Precipitation control and activation enhancement in boron-doped p <sup>+</sup> -BaSi <sub>2</sub> films grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2014, 104, .	1.5	32
46	Evaluation of band offset at amorphous-Si/BaSi <sub>2</sub> interfaces by hard x-ray photoelectron spectroscopy. <i>Journal of Applied Physics</i> , 2016, 119, .	1.1	32
47	Fabrication and characterization of BaSi <sub>2</sub> epitaxial films over 1 $\mu\text{m}$ in thickness on Si(111). <i>Japanese Journal of Applied Physics</i> , 2014, 53, 04ER04.	0.8	31
48	Improved Surface Quality of the Metal-Induced Crystallized Ge Seed Layer and Its Influence on Subsequent Epitaxy. <i>Crystal Growth and Design</i> , 2015, 15, 1535-1539.	1.4	30
49	Simple way of finding Ba to Si deposition rate ratios for high photoresponsivity in BaSi <sub>2</sub> films by Raman spectroscopy. <i>Applied Physics Express</i> , 2019, 12, 055506.	1.1	30
50	Al-Induced oriented-crystallization of Si films on quartz and its application to epitaxial template for Ge growth. <i>Solid-State Electronics</i> , 2011, 60, 7-12.	0.8	29
51	Evaluation of potential variations around grain boundaries in BaSi <sub>2</sub> epitaxial films by Kelvin probe force microscopy. <i>Applied Physics Letters</i> , 2013, 103, .	1.5	29
52	Polycrystalline thin-film transistors fabricated on high-mobility solid-phase-crystallized Ge on glass. <i>Applied Physics Letters</i> , 2019, 114, .	1.5	28
53	Negative spin polarization at the Fermi level in Fe <sub>4</sub> N epitaxial films by spin-resolved photoelectron spectroscopy. <i>Journal of Applied Physics</i> , 2012, 112, .	1.1	27
54	Millimeter-sized magnetic domains in perpendicularly magnetized ferrimagnetic Mn <sub>4</sub> N thin films grown on SrTiO <sub>3</sub> . <i>Japanese Journal of Applied Physics</i> , 2018, 57, 120310.	0.8	27

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55	Magnetic and magneto-transport properties of Mn <sub>4</sub> N thin films by Ni substitution and their possibility of magnetic compensation. <i>Journal of Applied Physics</i> , 2019, 125, .	1.1	27
56	Strong correlation between uniaxial magnetic anisotropic constant and in-plane tensile strain in Mn <sub>4</sub> N epitaxial films. <i>AIP Advances</i> , 2020, 10, .	0.6	27
57	N-type doping of BaSi <sub>2</sub> epitaxial films by phosphorus ion implantation and thermal annealing. <i>Thin Solid Films</i> , 2014, 557, 90-93.	0.8	26
58	Direct synthesis of multilayer graphene on an insulator by Ni-induced layer exchange growth of amorphous carbon. <i>Applied Physics Letters</i> , 2017, 110, .	1.5	26
59	High-quality multilayer graphene on an insulator formed by diffusion controlled Ni-induced layer exchange. <i>Applied Physics Letters</i> , 2017, 111, .	1.5	26
60	Spectroscopic evidence of photogenerated carrier separation by built-in electric field in Sb-doped n-BaSi <sub>2</sub> /B-doped p-BaSi <sub>2</sub> homojunction diodes. <i>Japanese Journal of Applied Physics</i> , 2018, 57, 050310.	0.8	26
61	Thermoelectric Inorganic SiGe Film Synthesized on Flexible Plastic Substrate. <i>ACS Applied Energy Materials</i> , 0, , .	2.5	26
62	High hole mobility ( $\approx 500 \text{ cm}^2/\text{Vs}$ ) polycrystalline Ge films on GeO <sub>2</sub> -coated glass and plastic substrates. <i>Applied Physics Express</i> , 2019, 12, 015508.	1.1	25
63	Defect-free single-crystal Ge island arrays on insulator by rapid-melting-growth combined with seed-positioning technique. <i>Applied Physics Letters</i> , 2009, 95, 112107.	1.5	24
64	X-ray magnetic circular dichroism of ferromagnetic Co <sub>4</sub> N epitaxial films on SrTiO <sub>3</sub> (001) substrates grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2011, 99, 252501.	1.5	23
65	Potential variations around grain boundaries in impurity-doped BaSi <sub>2</sub> epitaxial films evaluated by Kelvin probe force microscopy. <i>Journal of Applied Physics</i> , 2014, 116, .	1.1	23
66	Control of grain size and crystallinity of poly-Si films on quartz by Al-induced crystallization. <i>CrystEngComm</i> , 2017, 19, 2305-2311.	1.3	23
67	Advanced solid-phase crystallization for high-hole mobility (450) Tj ETQq1 1 0.784314 rgBT /Overlock 10 Tf 50 267 Td ( $\text{cm}^2/\text{Vs}$ ) 2018, 11, 031302.	1.1	23
68	Metal Catalysts for Layer-Exchange Growth of Multilayer Graphene. <i>ACS Applied Materials &amp; Interfaces</i> , 2018, 10, 41664-41669.	4.0	23
69	Magnetic reversal in rare-earth free Mn <sub>4</sub> N epitaxial films below and above Ni composition needed for magnetic compensation around room temperature. <i>Journal of Applied Physics</i> , 2020, 127, .	1.1	23
70	Strain effects on polycrystalline germanium thin films. <i>Scientific Reports</i> , 2021, 11, 8333.	1.6	23
71	N-type doping of BaSi <sub>2</sub> epitaxial films by arsenic ion implantation through a dose-dependent carrier generation mechanism. <i>Thin Solid Films</i> , 2014, 567, 105-108.	0.8	22
72	High-electron-mobility ( $370 \text{ cm}^2/\text{Vs}$ ) polycrystalline Ge on an insulator formed by As-doped solid-phase crystallization. <i>Scientific Reports</i> , 2019, 9, 16558.	1.6	22

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73	High Quality Single-Crystalline Ge-Rich SiGe on Insulator Structures by Si-Doping Controlled Rapid Melting Growth. Applied Physics Express, 2010, 3, 031301.	1.1	21
74	Defect-free Ge-on-insulator with (100), (110), and (111) orientations by growth-direction-selected rapid-melting growth. Applied Physics Letters, 2010, 97, .	1.5	21
75	Single-crystalline (100) Ge networks on insulators by rapid-melting growth along hexagonal mesh-pattern. Applied Physics Letters, 2011, 98, .	1.5	21
76	Dependence of crystal orientation in Al-induced crystallized poly-Si layers on SiO <sub>2</sub> insertion layer thickness. Journal of Crystal Growth, 2012, 356, 65-69.	0.7	21
77	Lattice and grain-boundary diffusions of boron atoms in BaSi <sub>2</sub> epitaxial films on Si(111). Journal of Applied Physics, 2013, 113, .	1.1	21
78	Vertically Aligned Ge Nanowires on Flexible Plastic Films Synthesized by (111)-Oriented Ge Seeded Vapor-Liquid-Solid Growth. ACS Applied Materials & Interfaces, 2015, 7, 18120-18124.	4.0	21
79	Epitaxial growth and magnetic properties of Fe <sub>4</sub> x Mn x N thin films grown on MgO(001) substrates by molecular beam epitaxy. Journal of Crystal Growth, 2018, 489, 20-23.	0.7	21
80	Record-High Hole Mobility Germanium on Flexible Plastic with Controlled Interfacial Reaction. ACS Applied Electronic Materials, 2022, 4, 269-275.	2.0	21
81	Growth and electric current loops in plants. Biophysical Chemistry, 1989, 33, 161-176.	1.5	20
82	Indentation-induced low-temperature solid-phase crystallization of Si <sub>1-x</sub> Gex (x=0-1) on insulator. Applied Physics Letters, 2009, 94, .	1.5	20
83	Direct synthesis of highly textured Ge on flexible polyimide films by metal-induced crystallization. Applied Physics Letters, 2014, 104, .	1.5	20
84	Evaluation of minority carrier diffusion length of undoped n-BaSi <sub>2</sub> epitaxial thin films on Si(001) substrates by electron-beam-induced-current technique. Japanese Journal of Applied Physics, 2014, 53, 078004.	0.8	20
85	Measurement of valence-band offset at native oxide/BaSi <sub>2</sub> interfaces by hard x-ray photoelectron spectroscopy. Journal of Applied Physics, 2016, 119, .	1.1	20
86	Significant photoresponsivity enhancement of polycrystalline BaSi <sub>2</sub> films formed on heated Si(111) substrates by sputtering. Applied Physics Express, 2018, 11, 071401.	1.1	20
87	Detection of local vibrational modes induced by intrinsic defects in undoped BaSi <sub>2</sub> light absorber layers using Raman spectroscopy. Journal of Applied Physics, 2018, 124, 025301.	1.1	20
88	Marked enhancement of the photoresponsivity and minority-carrier lifetime of BaS <sub>2</sub> passivated with atomic hydrogen. Physical Review Materials, 2019, 3, .	0.9	20
89	(100) Orientation-Controlled Ge Giant-Stripes on Insulating Substrates by Rapid-Melting Growth Combined with Si Micro-Seed Technique. Applied Physics Express, 2010, 3, 075603.	1.1	19
90	X-ray magnetic circular dichroism for Co <sub>x</sub> Fe <sub>4-x</sub> N (x=0, 3, 4) films grown by molecular beam epitaxy. Journal of Applied Physics, 2014, 115, 17C712.	1.1	19

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91	Formation of BaSi <sub>2</sub> heterojunction solar cells using transparent MoO <sub>3</sub> hole transport layers. Applied Physics Letters, 2015, 106, .	1.5	19
92	Effect of p-BaSi <sub>2</sub> layer thickness on the solar cell performance of p-BaSi <sub>2</sub> /n-Si heterojunction solar cells. Japanese Journal of Applied Physics, 2017, 56, 05DB03.	0.8	19
93	Low-Temperature (400 Å°C) Synthesis of Multilayer Graphene by Metal-Assisted Sputtering Deposition. ACS Omega, 2019, 4, 6677-6680.	1.6	19
94	Sb-doped crystallization of densified precursor for n-type polycrystalline Ge on an insulator with high carrier mobility. Applied Physics Letters, 2019, 114, .	1.5	19
95	350 Å°C synthesis of high-quality multilayer graphene on an insulator using Ni-induced layer exchange. Applied Physics Express, 2020, 13, 055502.	1.1	19
96	Molecular Beam Epitaxy of BaSi <sub>2</sub> Films with Grain Size over 4 μm on Si(111). Japanese Journal of Applied Physics, 2012, 51, 098003.	0.8	18
97	Molecular beam epitaxy of boron doped p-type BaSi <sub>2</sub> epitaxial films on Si(111) substrates for thin-film solar cells. Journal of Crystal Growth, 2013, 378, 201-204.	0.7	18
98	Local electronic states of Fe <sub>4</sub> N films revealed by x-ray absorption spectroscopy and x-ray magnetic circular dichroism. Journal of Applied Physics, 2015, 117, .	1.1	18
99	Low temperature synthesis of highly oriented p-type Si <sub>1-x</sub> Ge <sub>x</sub> (x=1) on an insulator by Al-induced layer exchange. Journal of Applied Physics, 2017, 122, .	1.1	18
100	Molecular beam epitaxy growth of Mn <sub>4</sub> Ni thin films on MgO(001) substrates and their magnetic properties. Journal of Crystal Growth, 2019, 507, 163-167.	0.7	18
101	Manipulation of saturation magnetization and perpendicular magnetic anisotropy in epitaxial C <sub>x</sub> O <sub>y</sub> M <sub>z</sub> (M = Mn, Fe, Ni) films. Applied Physics Letters, 2019, 115, 052401.	1.1	18
102	Negative Anisotropic Magnetoresistance in $\text{Fe}_{4}\text{N}$ Epitaxial Films on SrTiO <sub>3</sub> (001) Grown by Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 2012, 51, 068001.	0.8	17
103	Double-Layered Ge Thin Films on Insulators Formed by an Al-Induced Layer-Exchange Process. Crystal Growth and Design, 2013, 13, 3908-3912.	1.4	17
104	Large-Grained Polycrystalline (111) Ge Films on Insulators by Thickness-Controlled Al-Induced Crystallization. ECS Journal of Solid State Science and Technology, 2013, 2, Q195-Q199.	0.9	17
105	Orientation control of Ge thin films by underlayer-selected Al-induced crystallization. CrystEngComm, 2014, 16, 2578.	1.3	17
106	80 Å°C synthesis of thermoelectric nanocrystalline Ge film on flexible plastic substrate by Zn-induced layer exchange. Applied Physics Express, 2019, 12, 055501.	1.1	17
107	Magnetic compensation at two different composition ratios in rare-earth-free Mn <sub>4</sub> N ferrimagnetic films. Physical Review Materials, 2020, 4, .	0.9	17
108	Temperature dependent Al-induced crystallization of amorphous Ge thin films on SiO <sub>2</sub> substrates. Journal of Crystal Growth, 2013, 372, 189-192.	0.7	16

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109	Low-temperature crystallization of amorphous silicon and amorphous germanium by soft X-ray irradiation. <i>Thin Solid Films</i> , 2013, 534, 334-340.	0.8	16
110	Mechanism of strain relaxation in BaSi <sub>2</sub> epitaxial films on Si(111) substrates during post-growth annealing and application for film exfoliation. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013, 10, 1677-1680.	0.8	16
111	Photoresponse properties of undoped BaSi <sub>2</sub> epitaxial layers on n <sup>+</sup> -BaSi <sub>2</sub> /p <sup>+</sup> -Si(001) by molecular beam epitaxy. <i>Japanese Journal of Applied Physics</i> , 2014, 53, 058007.	0.8	16
112	Growth promotion of Al-induced crystallized Ge films on insulators by insertion of a Ge membrane below the Al layer. <i>Thin Solid Films</i> , 2014, 557, 143-146.	0.8	16
113	Epitaxial growth and magnetic properties of Ni <sub>x</sub> Fe <sub>4-x</sub> N (x=0, 1, 3, and 4) films on SrTiO <sub>3</sub> (001) substrates. <i>Journal of Applied Physics</i> , 2016, 120, .	1.1	16
114	Silver-induced layer exchange for polycrystalline germanium on a flexible plastic substrate. <i>Journal of Applied Physics</i> , 2017, 122, .	1.1	16
115	Three-step growth of highly photoresponsive BaSi <sub>2</sub> light absorbing layers with uniform Ba to Si atomic ratios. <i>Journal of Applied Physics</i> , 2019, 126, .	1.1	16
116	Mesh-shape-and-size controlled rapid-melting growth for the formation of single-crystalline (100), (110), and (111) Ge networks on insulators. <i>Applied Physics Letters</i> , 2011, 98, .	1.5	15
117	Epitaxy of Orthorhombic BaSi <sub>2</sub> with Preferential In-Plane Crystal Orientation on Si(001): Effects of Vicinal Substrate and Annealing Temperature. <i>Japanese Journal of Applied Physics</i> , 2012, 51, 095501.	0.8	15
118	Structural study on phosphorus doping of BaSi <sub>2</sub> epitaxial films by ion implantation. <i>Thin Solid Films</i> , 2013, 534, 470-473.	0.8	15
119	Fabrication and characterizations of phosphorus-doped n-type BaSi <sub>2</sub> epitaxial films grown by molecular beam epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013, 10, 1753-1755.	0.8	15
120	Hard x-ray photoelectron spectroscopy study on valence band structure of semiconducting BaSi <sub>2</sub> . <i>Journal of Applied Physics</i> , 2013, 114, 123702.	1.1	15
121	Solid-phase crystallization of densified amorphous GeSn leading to high hole mobility (540 cm <sup>2</sup> /V s). <i>Applied Physics Letters</i> , 2019, 114, .	1.5	15
122	Orientation control of intermediate-composition SiGe on insulator by low-temperature Al-induced crystallization. <i>Scripta Materialia</i> , 2016, 122, 86-88.	2.6	14
123	Enhanced spectral response of semiconducting BaSi <sub>2</sub> films by oxygen incorporation. <i>Thin Solid Films</i> , 2017, 629, 17-21.	0.8	14
124	Molecular beam epitaxy of Co <sub>1-x</sub> Fe <sub>4x</sub> N (0.4<x<2.9) thin films on SrTiO <sub>3</sub> (001) substrates. <i>Journal of Crystal Growth</i> , 2012, 357, 53-57.	0.7	13
125	Rotational and vibrational temperatures in a hydrogen discharge with a magnetic X-point. <i>Physics of Plasmas</i> , 2012, 19, 123503.	0.7	13
126	High-quality formation of multiply stacked SiGe-on-insulator structures by temperature-modulated successive rapid-melting-growth. <i>Applied Physics Letters</i> , 2013, 102, .	1.5	13



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127	High-hole mobility Si <sub>1</sub> -Ge (0.1 at% x at% 1) on an insulator formed by advanced solid-phase crystallization. Journal of Alloys and Compounds, 2018, 766, 417-420.	2.8	13
128	Investigation of defect levels in BaSi <sub>2</sub> epitaxial films by photoluminescence and the effect of atomic hydrogen passivation. Journal of Physics Communications, 2019, 3, 075005.	0.5	13
129	Zn-induced layer exchange of p- and n-type nanocrystalline SiGe layers for flexible thermoelectrics. Applied Physics Letters, 2020, 116, .	1.5	13
130	Atomic hydrogen passivation for photoresponsivity enhancement of boron-doped p-BaSi <sub>2</sub> films and performance improvement of boron-doped p-BaSi <sub>2</sub> /n-Si heterojunction solar cells. Journal of Applied Physics, 2020, 127, .	1.1	13
131	Formation of high-photoresponsivity BaSi <sub>2</sub> films on glass substrate by radio-frequency sputtering for solar cell applications. Journal Physics D: Applied Physics, 2021, 54, 135106.	1.3	13
132	Investigation of electrically active defects in undoped BaSi <sub>2</sub> light absorber layers using deep-level transient spectroscopy. Japanese Journal of Applied Physics, 2018, 57, 075801.	0.8	12
133	Perpendicular magnetic anisotropy in ferrimagnetic Mn <sub>4</sub> N films grown on (LaAlO <sub>3</sub> ) <sub>0.3</sub> (Sr <sub>2</sub> TaAlO <sub>6</sub> ) <sub>0.7</sub> substrates by molecular beam epitaxy. Journal of Crystal Growth, 2020, 535, 125566.	0.7	12
134	Structural Study of BF <sub>2</sub> Ion Implantation and Post Annealing of BaSi <sub>2</sub> Epitaxial Films. Japanese Journal of Applied Physics, 2011, 50, 121202.	0.8	11
135	Electronic structures and magnetic moments of Co <sub>3</sub> FeN thin films grown by molecular beam epitaxy. Applied Physics Letters, 2013, 103, .	1.5	11
136	Characterization of defect levels in undoped n-BaSi <sub>2</sub> epitaxial films on Si(111) by deep-level transient spectroscopy. Japanese Journal of Applied Physics, 2015, 54, 07JE01.	0.8	11
137	Reduction in interface defect density in p-BaSi <sub>2</sub> /n-Si heterojunction solar cells by a modified pretreatment of the Si substrate. Japanese Journal of Applied Physics, 2018, 57, 025501.	0.8	11
138	Impact of deposition pressure and two-step growth technique on the photoresponsivity enhancement of polycrystalline BaSi <sub>2</sub> films formed by sputtering. Applied Physics Express, 2019, 12, 021004.	1.1	11
139	Spontaneous formation of the spatial pattern of electric potential in biological systems. Ferroelectrics, 1988, 86, 269-279.	0.3	10
140	Self-organization of Ge(111)/Al/glass structures through layer exchange in metal-induced crystallization. CrystEngComm, 2014, 16, 9590-9595.	1.3	10
141	Influence of Substrate on Crystal Orientation of Large-Grained Si Thin Films Formed by Metal-Induced Crystallization. International Journal of Photoenergy, 2015, 2015, 1-7.	1.4	10
142	Growth and magnetic properties of epitaxial Fe <sub>4</sub> N films on insulators possessing lattice spacing close to Si(001) plane. Journal of Crystal Growth, 2016, 455, 66-70.	0.7	10
143	Multilayer graphene on insulator formed by Co-induced layer exchange. Japanese Journal of Applied Physics, 2017, 56, 05DE03.	0.8	10
144	Improving the photoresponse spectra of BaSi <sub>2</sub> layers by capping with hydrogenated amorphous Si layers prepared by radio-frequency hydrogen plasma. AIP Advances, 2018, 8, 055306.	0.6	10

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145	High photoresponsivity in a GaAs film synthesized on glass using a pseudo-single-crystal Ge seed layer. Applied Physics Letters, 2019, 114, .	1.5	10
146	Multilayer Graphene Battery Anodes on Plastic Sheets for Flexible Electronics. ACS Applied Energy Materials, 2020, 3, 8410-8414.	2.5	10
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